

N-Channel 100-V (D-S) MOSFET

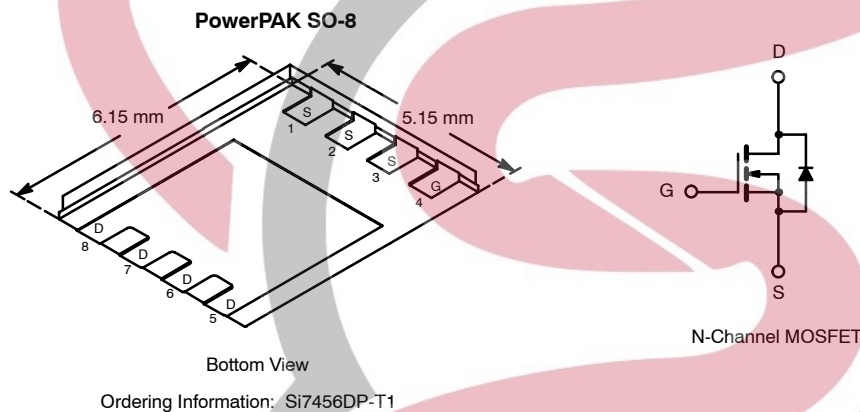
PRODUCT SUMMARY		
V_{DS} (V)	$r_{DS(on)}$ (Ω)	I_D (A)
100	0.025 @ $V_{GS} = 10$ V	9.3
	0.028 @ $V_{GS} = 6.0$ V	8.8

FEATURES

- TrenchFET® Power MOSFETS
- New Low Thermal Resistance PowerPAK® Package with Low 1.07-mm Profile
- PWM Optimized for Fast Switching
- 100% R_g Tested

APPLICATIONS

- Primary Side Switch for High Density DC/DC
- Telecom/Server 48-V, Full-/Half-Bridge DC/DC
- Industrial and 42-V Automotive



ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED)					
Parameter	Symbol	10 secs	Steady State	Unit	
Drain-Source Voltage	V_{DS}	100		V	
Gate-Source Voltage	V_{GS}	± 20			
Continuous Drain Current ($T_J = 150^\circ\text{C}$) ^a	I_D	$T_A = 25^\circ\text{C}$	9.3	5.7	A
		$T_A = 85^\circ\text{C}$	6.7	4.1	
Pulsed Drain Current	I_{DM}	40		mJ	
Avalanche Current	I_{AS}	30			
Single Avalanche Energy (Duty Cycle $\leq 1\%$)	E_{AS}	$L = 0.1$ mH	45		
Continuous Source Current (Diode Conduction) ^a			I_S	4.3	1.6
Maximum Power Dissipation ^a	P_D	$T_A = 25^\circ\text{C}$	5.2	1.9	W
		$T_A = 85^\circ\text{C}$	2.7	1.0	
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55 to 150		$^\circ\text{C}$	

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Typical	Maximum	Unit	
Maximum Junction-to-Ambient ^a	R_{thJA}	$t \leq 10$ sec	19	24	$^\circ\text{C/W}$
		Steady State	52	65	
Maximum Junction-to-Case	R_{thJC}	1.5	1.8		

Notes

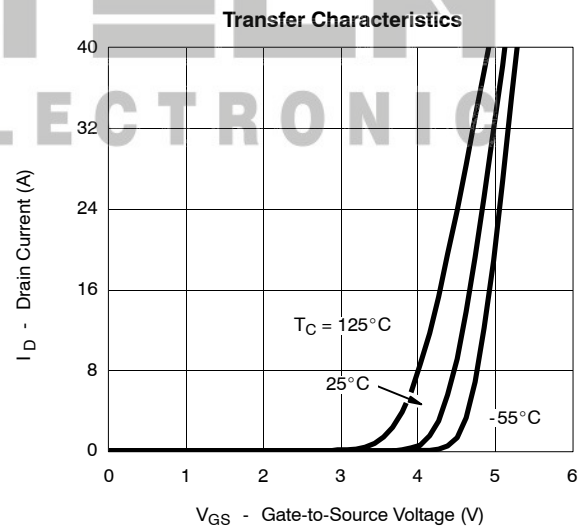
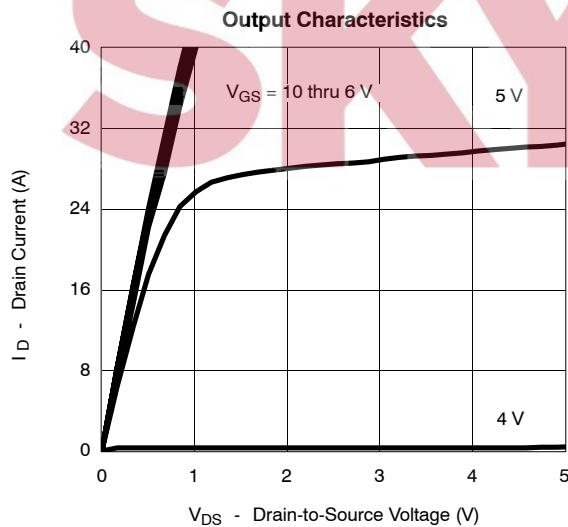
a. Surface Mounted on 1" x 1" FR4 Board.

SPECIFICATIONS (T _J = 25 °C UNLESS OTHERWISE NOTED)						
Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Static						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA	2			V
Gate-Body Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ±20 V			±100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 100 V, V _{GS} = 0 V			1	μA
		V _{DS} = 100 V, V _{GS} = 0 V, T _J = 85 °C			20	
On-State Drain Current ^a	I _{D(on)}	V _{DS} ≥ 5 V, V _{GS} = 10 V	40			A
Drain-Source On-State Resistance ^a	r _{DS(on)}	V _{GS} = 10 V, I _D = 9.3 A		0.021	0.025	Ω
		V _{GS} = 6.0 V, I _D = 8.8 A		0.023	0.028	
Forward Transconductance ^a	g _{fs}	V _{DS} = 15 V, I _D = 9.3 A		35		S
Diode Forward Voltage ^a	V _{SD}	I _S = 4.3 A, V _{GS} = 0 V		0.8	1.2	V
Dynamic^b						
Total Gate Charge	Q _g	V _{DS} = 50 V, V _{GS} = 10 V, I _D = 9.3 A		36	44	nC
Gate-Source Charge	Q _{gs}		10			
Gate-Drain Charge	Q _{gd}		8.6			
Gate Resistance	R _g		0.5	1.27	2.1	Ω
Turn-On Delay Time	t _{d(on)}	V _{DD} = 50 V, R _L = 50 Ω I _D ≅ 1 A, V _{GEN} = 10 V, R _G = 6 Ω		20	40	ns
Rise Time	t _r		10	20		
Turn-Off Delay Time	t _{d(off)}		46	90		
Fall Time	t _f		26	50		
Source-Drain Reverse Recovery Time	t _{rr}		I _F = 4.3 A, di/dt = 100 A/μs		50	

Notes

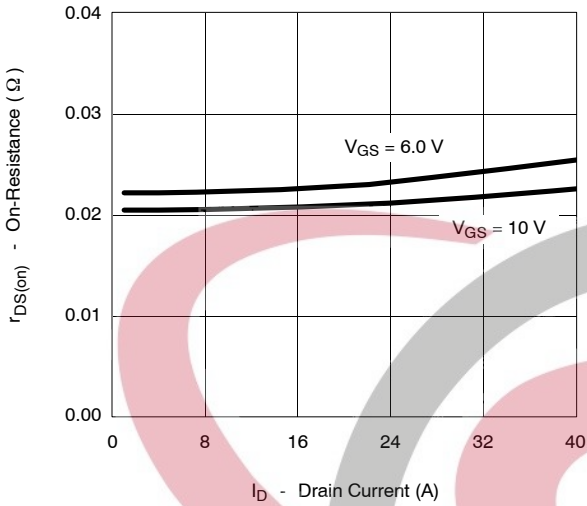
- a. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2%.
- b. Guaranteed by design, not subject to production testing.

TYPICAL CHARACTERISTICS (25 °C UNLESS NOTED)

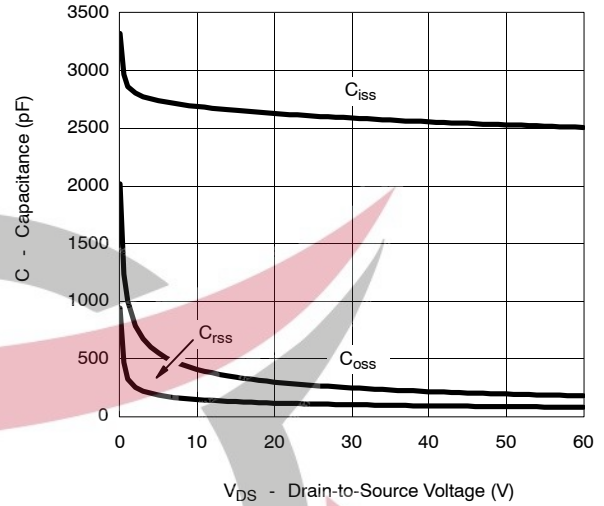


TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)

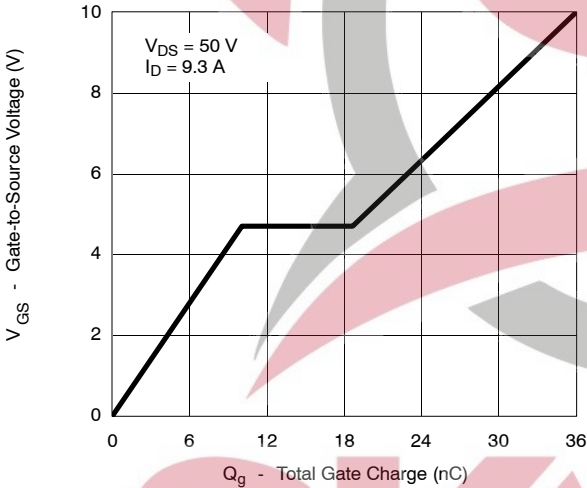
On-Resistance vs. Drain Current



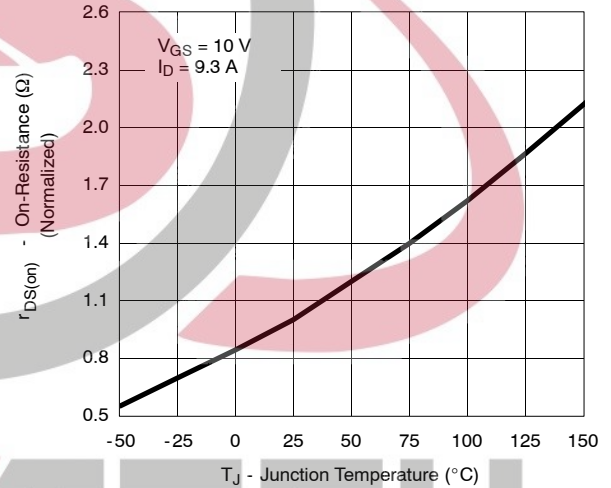
Capacitance



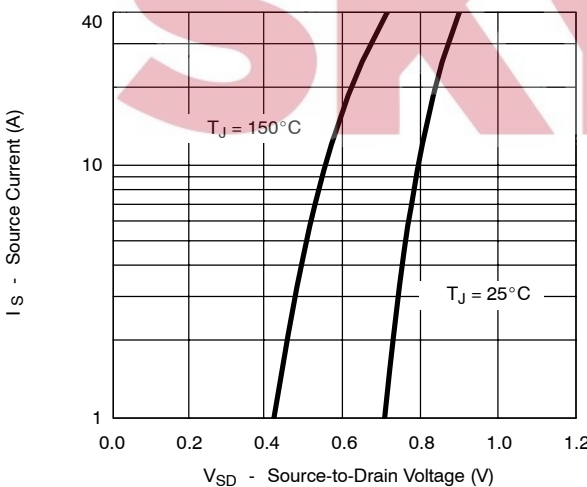
Gate Charge



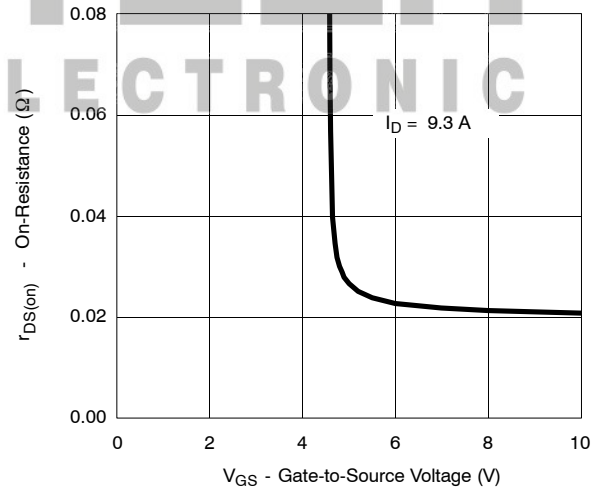
On-Resistance vs. Junction Temperature



Source-Drain Diode Forward Voltage



On-Resistance vs. Gate-to-Source Voltage



TYPICAL CHARACTERISTICS (25 °C UNLESS NOTED)

